

CPC COOPERATIVE PATENT CLASSIFICATION

B PERFORMING OPERATIONS; TRANSPORTING

(NOTES omitted)

MICROSTRUCTURAL TECHNOLOGY; NANOTECHNOLOGY

B81 MICROSTRUCTURAL TECHNOLOGY

(NOTES omitted)

B81C PROCESSES OR APPARATUS SPECIALLY ADAPTED FOR THE MANUFACTURE OR TREATMENT OF MICROSTRUCTURAL DEVICES OR SYSTEMS (making microcapsules or microballoons [B01J 13/02](#); processes or apparatus peculiar to the manufacture or treatment of piezo-electric, electrostrictive or magnetostrictive element per se [H10N 30/01](#))

NOTES

- This subclass does not cover:
 - processes or apparatus for the manufacture or treatment of purely electrical or electronic devices, which are covered by section [H](#), e.g. group [H01L 21/00](#);
 - processes or apparatus involving the manipulation of single atoms or molecules, which are covered by group [B82B 3/00](#).
- In this subclass, local "residual" subgroups, e.g. [B81C 1/00126](#), are used with the following purpose.
 When classifying a document which does not fit in any of a set of subgroups with the same dot-level, the document should be classified in the residual group, if present, and not in the group at the hierarchical level one dot above.
 In the example, the document shall be classified in [B81C 1/00126](#) and not in [B81C 1/00023](#) as [B81C 1/00126](#) is "residual" to [B81C 1/00031-B81C 1/00119](#)

1/00	Manufacture or treatment of devices or systems in or on a substrate (B81C 3/00 takes precedence)	1/00119 . . . {Arrangement of basic structures like cavities or channels, e.g. suitable for microfluidic systems}
1/00007	. {Assembling automatically hinged components, i.e. self-assembly processes (self-assembly mechanisms B81B 7/0003)}	1/00126 . . . {Static structures not provided for in groups B81C 1/00031 - B81C 1/00119 }
1/00015	. {for manufacturing microsystems}	1/00134 . . {comprising flexible or deformable structures (manufacture of MEMS devices for specific applications, see relevant places, e.g. gyroscopes G01C 19/5719 , pressure sensors G01L 9/0042 , accelerometers G01P 15/0802 , acoustic transducers or diaphragms therefor H04R 31/00)}
1/00023	. . {without movable or flexible elements (array of static structures for functionalising surfaces in B81C 1/00206 ; manufacture of MEMS devices for specific applications, see relevant places, e.g. microreactors B01J 19/0093 , lab-on-chip B01L 3/5027 , micromixers B01F 33/30)}	1/00142 . . . {Bridges (deformable micromirrors G02B 26/0841)}
1/00031	. . . {Regular or irregular arrays of nanoscale structures, e.g. etch mask layer (photomechanical, e.g. photolithographic, production of textured or patterned surfaces G03F 7/00 ; lithographic processes for making patterned surfaces using printing and stamping G03F 7/0002)}	1/0015 . . . {Cantilevers (switches using MEMS H01H 1/0036 ; electrostatic relays using micromechanics H01H 59/0009 ; microelectro-mechanical resonators H03H 9/02244)}
1/00039	. . . {Anchors}	1/00158 . . . {Diaphragms, membranes (manufacture process for semi-permeable inorganic membranes B01D 67/0039)}
1/00047	. . . {Cavities}	1/00166 . . . {Electrodes}
1/00055	. . . {Grooves}	1/00174 . . . {See-saws}
1/00063 {Trenches}	1/00182 . . . {Arrangements of deformable or non-deformable structures, e.g. membrane and cavity for use in a transducer}
1/00071 {Channels}	1/0019 . . . {Flexible or deformable structures not provided for in groups B81C 1/00142 - B81C 1/00182 }
1/00079 {Grooves not provided for in groups B81C 1/00063 - B81C 1/00071 }	1/00198 . . {comprising elements which are movable in relation to each other, e.g. comprising slidable or rotatable elements}
1/00087	. . . {Holes}	1/00206 . . {Processes for functionalising a surface, e.g. provide the surface with specific mechanical, chemical or biological properties}
1/00095	. . . {Interconnects}	
1/00103	. . . {Structures having a predefined profile, e.g. sloped or rounded grooves}	
1/00111	. . . {Tips, pillars, i.e. raised structures (microneedles A61M 37/0015)}	

- 1/00214 . . {Processes for the simultaneous manufacturing of a network or an array of similar microstructural devices}
- 1/00222 . . {Integrating an electronic processing unit with a micromechanical structure}
- 1/0023 . . . {Packaging together an electronic processing unit die and a micromechanical structure die (MEMS packages [B81B 7/0032](#); MEMS packaging processes [B81C 1/00261](#))}
- 1/00238 . . . {Joining a substrate with an electronic processing unit and a substrate with a micromechanical structure}
- 1/00246 . . . {Monolithic integration, i.e. micromechanical structure and electronic processing unit are integrated on the same substrate}
- 1/00253 . . . {Processes for integrating an electronic processing unit with a micromechanical structure not provided for in [B81C 1/0023](#) - [B81C 1/00246](#)}
- 1/00261 . . {Processes for packaging MEMS devices (MEMS packages [B81B 7/0032](#), packaging of smart-MEMS [B81C 1/0023](#))}
- 1/00269 . . . {Bonding of solid lids or wafers to the substrate}
- 1/00277 . . . {for maintaining a controlled atmosphere inside of the cavity containing the MEMS}
- 1/00285 {using materials for controlling the level of pressure, contaminants or moisture inside of the package, e.g. getters}
- 1/00293 {maintaining a controlled atmosphere with processes not provided for in [B81C 1/00285](#)}
- 1/00301 . . . {Connecting electric signal lines from the MEMS device with external electrical signal lines, e.g. through vias}
- 1/00309 . . . {suitable for fluid transfer from the MEMS out of the package or *vice versa*, e.g. transfer of liquid, gas, sound}
- 1/00317 . . . {Packaging optical devices}
- 1/00325 . . . {for reducing stress inside of the package structure}
- 1/00333 . . . {Aspects relating to packaging of MEMS devices, not covered by groups [B81C 1/00269](#) - [B81C 1/00325](#)}
- 1/00341 . . {Processes for manufacturing microsystems not provided for in groups [B81C 1/00023](#) - [B81C 1/00261](#)}
- 1/00349 . {Creating layers of material on a substrate}
- 1/00357 . . {involving bonding one or several substrates on a non-temporary support, e.g. another substrate}
- 1/00365 . . {having low tensile stress between layers}
- 1/00373 . . {Selective deposition, e.g. printing or microcontact printing}
- 1/0038 . . {Processes for creating layers of materials not provided for in groups [B81C 1/00357](#) - [B81C 1/00373](#)}
- 1/00388 . {Etch mask forming}
- 1/00396 . . {Mask characterised by its composition, e.g. multilayer masks}
- 1/00404 . . {Mask characterised by its size, orientation or shape}
- 1/00412 . . {Mask characterised by its behaviour during the etching process, e.g. soluble masks}
- 1/0042 . . {Compensation masks in orientation dependent etching}
- 1/00428 . . {Etch mask forming processes not provided for in groups [B81C 1/00396](#) - [B81C 1/0042](#)}
- 1/00436 . {Shaping materials, i.e. techniques for structuring the substrate or the layers on the substrate}
- 1/00444 . . {Surface micromachining, i.e. structuring layers on the substrate}
- 1/0046 . . . {using stamping, e.g. imprinting (nanoimprinting for making etch masks [G03F 7/0002](#))}
- 1/00468 . . . {Releasing structures}
- 1/00476 {removing a sacrificial layer ([B81C 1/00912](#) takes precedence)}
- 1/00484 {Processes for releasing structures not provided for in group [B81C 1/00476](#)}
- 1/00492 . . . {Processes for surface micromachining not provided for in groups [B81C 1/0046](#) - [B81C 1/00484](#)}
- 1/005 . . {Bulk micromachining}
- 1/00507 . . . {Formation of buried layers by techniques other than deposition, e.g. by deep implantation of elements (SIMOX techniques [H01L 21/762](#))}
- 1/00515 . . . {Bulk micromachining techniques not provided for in [B81C 1/00507](#)}
- 1/00523 . . {Etching material}
- 1/00531 . . . {Dry etching}
- 1/00539 . . . {Wet etching}
- 1/00547 . . . {Etching processes not provided for in groups [B81C 1/00531](#) - [B81C 1/00539](#)}
- 1/00555 . . {Achieving a desired geometry, i.e. controlling etch rates, anisotropy or selectivity ([B81C 1/00023](#) - [B81C 1/0019](#) take precedence)}
- 1/00563 . . . {Avoid or control over-etching}
- 1/00571 {Avoid or control under-cutting}
- 1/00579 {Avoid charge built-up}
- 1/00587 {Processes for avoiding or controlling over-etching not provided for in [B81C 1/00571](#) - [B81C 1/00579](#)}
- 1/00595 . . . {Control etch selectivity}
- 1/00603 . . . {Aligning features and geometries on both sides of a substrate, e.g. when double side etching}
- 1/00611 . . . {Processes for the planarisation of structures (planarising depositions [C23C](#), [H01L](#))}
- 1/00619 . . . {Forming high aspect ratio structures having deep steep walls}
- 1/00626 . . . {Processes for achieving a desired geometry not provided for in groups [B81C 1/00563](#) - [B81C 1/00619](#)}
- 1/00634 . . {Processes for shaping materials not provided for in groups [B81C 1/00444](#) - [B81C 1/00626](#)}
- 1/00642 . {for improving the physical properties of a device}
- 1/0065 . . {Mechanical properties}
- 1/00658 . . . {Treatments for improving the stiffness of a vibrating element}
- 1/00666 . . . {Treatments for controlling internal stress or strain in MEMS structures}
- 1/00674 . . . {Treatments for improving wear resistance}
- 1/00682 . . . {Treatments for improving mechanical properties, not provided for in [B81C 1/00658](#) - [B81C 1/0065](#)}
- 1/0069 . . {Thermal properties, e.g. improve thermal insulation}

- 1/00698 . . {Electrical characteristics, e.g. by doping materials}
- 1/00706 . . {Magnetic properties}
- 1/00714 . . {Treatment for improving the physical properties not provided for in groups [B81C 1/0065](#) - [B81C 1/00706](#)}
- 1/00777 . {Preserve existing structures from alteration, e.g. temporary protection during manufacturing}
- 1/00785 . . {Avoid chemical alteration, e.g. contamination, oxidation or unwanted etching ([B81C 1/00563](#) - [B81C 1/00595](#) take precedence)}
- 1/00793 . . . {Avoid contamination, e.g. absorption of impurities or oxidation}
- 1/00801 . . . {Avoid alteration of functional structures by etching, e.g. using a passivation layer or an etch stop layer ([B81C 1/00595](#), [B81C 1/00468](#) take precedence)}
- 1/00809 . . . {Methods to avoid chemical alteration not provided for in groups [B81C 1/00793](#) - [B81C 1/00801](#)}
- 1/00817 . . {Avoid thermal destruction}
- 1/00825 . . {Protect against mechanical threats, e.g. against shocks, or residues ([B81C 1/00261](#) take precedence)}
- 1/00833 . . {Methods for preserving structures not provided for in groups [B81C 1/00785](#) - [B81C 1/00825](#)}
- 1/00841 . {Cleaning during or after manufacture (cleaning of semiconductor devices [H01L 21/306](#))}
- 1/00849 . . {during manufacture}
- 1/00857 . . {after manufacture, e.g. back-end of the line process}
- 1/00865 . {Multistep processes for the separation of wafers into individual elements}
- 1/00873 . . {characterised by special arrangements of the devices, allowing an easier separation}
- 1/0088 . . {Separation allowing recovery of the substrate or a part of the substrate, e.g. epitaxial lift-off}
- 1/00888 . . {Multistep processes involving only mechanical separation, e.g. grooving followed by cleaving}
- 1/00896 . . {Temporary protection during separation into individual elements}
- 1/00904 . . {Multistep processes for the separation of wafers into individual elements not provided for in groups [B81C 1/00873](#) - [B81C 1/00896](#)}
- 1/00912 . {Treatments or methods for avoiding stiction of flexible or moving parts of MEMS}
- 1/0092 . . {For avoiding stiction during the manufacturing process of the device, e.g. during wet etching}
- 1/00928 . . . {Eliminating or avoiding remaining moisture after the wet etch release of the movable structure}
- 1/00936 . . . {Releasing the movable structure without liquid etchant}
- 1/00944 . . . {Maintaining a critical distance between the structures to be released}
- 1/00952 . . . {Treatments or methods for avoiding stiction during the manufacturing process not provided for in groups [B81C 1/00928](#) - [B81C 1/00944](#)}
- 1/0096 . . {For avoiding stiction when the device is in use, i.e. after manufacture has been completed}
- 1/00968 . . . {Methods for breaking the stiction bond}
- 1/00976 . . . {Control methods for avoiding stiction, e.g. controlling the bias voltage}
- 1/00984 . . . {Methods for avoiding stiction when the device is in use not provided for in groups [B81C 1/00968](#) - [B81C 1/00976](#)}
- 1/00992 . . {Treatments or methods for avoiding stiction of flexible or moving parts of MEMS not provided for in groups [B81C 1/0092](#) - [B81C 1/00984](#)}
- 3/00 Assembling of devices or systems from individually processed components**
- 3/001 . {Bonding of two components}
- 3/002 . {Aligning microparts}
- 3/004 . . {Active alignment, i.e. moving the elements in response to the detected position of the elements using internal or external actuators}
- 3/005 . . {Passive alignment, i.e. without a detection of the position of the elements or using only structural arrangements or thermodynamic forces}
- 3/007 . . {Methods for aligning microparts not provided for in groups [B81C 3/004](#) - [B81C 3/005](#)}
- 3/008 . {Aspects related to assembling from individually processed components, not covered by groups [B81C 3/001](#) - [B81C 3/002](#)}
- 99/00 Subject matter not provided for in other groups of this subclass**
- 99/0005 . {Apparatus specially adapted for the manufacture or treatment of microstructural devices or systems, or methods for manufacturing the same}
- 99/001 . . {for cutting, cleaving or grinding}
- 99/0015 . . {for microextrusion (extrusion heads in general [B29C 48/30](#))}
- 99/002 . . {Apparatus for assembling MEMS, e.g. micromanipulators ([micromanipulators per se B25J 7/00](#))}
- 99/0025 . . {Apparatus specially adapted for the manufacture or treatment of microstructural devices or systems not provided for in [B81C 99/001](#) - [B81C 99/002](#)}
- 99/003 . {Characterising MEMS devices, e.g. measuring and identifying electrical or mechanical constants}
- 99/0035 . {Testing}
- 99/004 . . {during manufacturing}
- 99/0045 . . {End test of the packaged device}
- 99/005 . . {Test apparatus}
- 99/0055 . {Manufacturing logistics}
- 99/006 . . {Design; Simulation}
- 99/0065 . . {Process control; Yield prediction}
- 99/007 . . {Marking}
- 99/0075 . {Manufacture of substrate-free structures}
- 99/008 . . {separating the processed structure from a mother substrate}
- 99/0085 . . {using moulds and master templates, e.g. for hot-embossing}
- 99/009 . . {Manufacturing the stamps or the moulds}
- 99/0095 . . {Aspects relating to the manufacture of substrate-free structures, not covered by groups [B81C 99/008](#) - [B81C 99/009](#)}
- 2201/00 Manufacture or treatment of microstructural devices or systems**
- 2201/01 . in or on a substrate
- 2201/0101 . . Shaping material; Structuring the bulk substrate or layers on the substrate; Film patterning
- 2201/0102 . . . Surface micromachining
- 2201/0104 Chemical-mechanical polishing [CMP]
- 2201/0105 Sacrificial layer

2201/0107	Sacrificial metal	2201/0164	by doping the layer
2201/0108	Sacrificial polymer, ashing of organics	2201/0166	by ion implantation
2201/0109	Sacrificial layers not provided for in B81C 2201/0107 - B81C 2201/0108	2201/0167	by adding further layers of materials having complementary strains, i.e. compressive or tensile strain
2201/0111	Bulk micromachining	2201/0169	by post-annealing
2201/0112	Bosch process	2201/017	Methods for controlling internal stress of deposited layers not provided for in B81C 2201/0164 - B81C 2201/0169
2201/0114	Electrochemical etching, anodic oxidation	2201/0171	Doping materials
2201/0115	Porous silicon	2201/0173	Thermo-migration of impurities from a solid, e.g. from a doped deposited layer
2201/0116	Thermal treatment for structural rearrangement of substrate atoms, e.g. for making buried cavities	2201/0174	for making multi-layered devices, film deposition or growing
2201/0118	Processes for the planarization of structures	2201/0176	Chemical vapour Deposition
2201/0119	involving only addition of materials, i.e. additive planarization	2201/0177	Epitaxy, i.e. homo-epitaxy, hetero-epitaxy, GaAs-epitaxy
2201/0121	involving addition of material followed by removal of parts of said material, i.e. subtractive planarization	2201/0178	Oxidation
2201/0122	Selective addition	2201/018	Plasma polymerization, i.e. monomer or polymer deposition
2201/0123	Selective removal	2201/0181	Physical Vapour Deposition [PVD], i.e. evaporation, sputtering, ion plating or plasma assisted deposition, ion cluster beam technology
2201/0125	Blanket removal, e.g. polishing	2201/0183	Selective deposition
2201/0126	Processes for the planarization of structures not provided for in B81C 2201/0119 - B81C 2201/0125	2201/0184	Digital lithography, e.g. using an inkjet print-head
2201/0128	Processes for removing material	2201/0185	Printing, e.g. microcontact printing
2201/0129	Diamond turning	2201/0187	Controlled formation of micro- or nanostructures using a template positioned on a substrate
2201/013	Etching	2201/0188	Selective deposition techniques not provided for in B81C 2201/0184 - B81C 2201/0187
2201/0132	Dry etching, i.e. plasma etching, barrel etching, reactive ion etching [RIE], sputter etching or ion milling	2201/019	Bonding or gluing multiple substrate layers
2201/0133	Wet etching	2201/0191	Transfer of a layer from a carrier wafer to a device wafer
2201/0135	Controlling etch progression	2201/0192	by cleaving the carrier wafer
2201/0136	by doping limited material regions	2201/0194	the layer being structured
2201/0138	Monitoring physical parameters in the etching chamber, e.g. pressure, temperature or gas composition	2201/0195	the layer being unstructured
2201/0139	with the electric potential of an electrochemical etching	2201/0197	Processes for making multi-layered devices not provided for in groups B81C 2201/0176 - B81C 2201/0192
2201/014	by depositing an etch stop layer, e.g. silicon nitride, silicon oxide, metal	2201/0198	for making a masking layer
2201/0142	Processes for controlling etch progression not provided for in B81C 2201/0136 - B81C 2201/014	2201/03	Processes for manufacturing substrate-free structures
2201/0143	Focussed beam, i.e. laser, ion or e-beam	2201/032	LIGA process
2201/0145	Spark erosion	2201/034	Moulding
2201/0146	Processes for removing material not provided for in B81C 2201/0129 - B81C 2201/0145	2201/036	Hot embossing
2201/0147	Film patterning	2201/038	Processes for manufacturing substrate-free structures not provided for in B81C 2201/034 - B81C 2201/036
2201/0149	Forming nanoscale microstructures using auto-arranging or self-assembling material	2201/05	Temporary protection of devices or parts of the devices during manufacturing
2201/015	Imprinting	2201/053	Depositing a protective layers
2201/0152	Step and Flash imprinting, UV imprinting	2201/056	Releasing structures at the end of the manufacturing process
2201/0153	Imprinting techniques not provided for in B81C 2201/0152	2201/11	Treatments for avoiding stiction of elastic or moving parts of MEMS
2201/0154	other processes for film patterning not provided for in B81C 2201/0149 - B81C 2201/015	2201/112	Depositing an anti-stiction or passivation coating, e.g. on the elastic or moving parts
2201/0156	Lithographic techniques	2201/115	Roughening a surface
2201/0157	Gray-scale mask technology	2201/117	Using supercritical fluid, e.g. carbon dioxide, for removing sacrificial layers
2201/0159	Lithographic techniques not provided for in B81C 2201/0157			
2201/016	Passivation			
2201/0161	Controlling physical properties of the material			
2201/0163	Controlling internal stress of deposited layers			

2203/00	Forming microstructural systems	
2203/01	. Packaging MEMS	
2203/0109	. . Bonding an individual cap on the substrate	
2203/0118	. . Bonding a wafer on the substrate, i.e. where the cap consists of another wafer	
2203/0127	. . Using a carrier for applying a plurality of packaging lids to the system wafer	
2203/0136	. . Growing or depositing of a covering layer	
2203/0145	. . Hermetically sealing an opening in the lid	
2203/0154	. . Moulding a cap over the MEMS device	
2203/0163	. . Reinforcing a cap, e.g. with ribs	
2203/0172	. . Seals	
2203/0181	. . . Using microheaters for bonding the lid	
2203/019	. . . characterised by the material or arrangement of seals between parts	
2203/03	. Bonding two components	
2203/031	. . Anodic bondings	
2203/032	. . Gluing	
2203/033	. . Thermal bonding	
2203/035	. . . Soldering	
2203/036	. . . Fusion bonding	
2203/037	. . . Thermal bonding techniques not provided for in B81C 2203/035 - B81C 2203/036	
2203/038	. . Bonding techniques not provided for in B81C 2203/031 - B81C 2203/037	
2203/05	. Aligning components to be assembled	
2203/051	. . Active alignment, e.g. using internal or external actuators, magnets, sensors, marks or marks detectors	
2203/052	. . Passive alignment, i.e. using only structural arrangements or thermodynamic forces without an internal or external apparatus	
2203/054	. . . using structural alignment aids, e.g. spacers, interposers, male/female parts, rods or balls	
2203/055	. . . using the surface tension of fluid solder to align the elements	
2203/057	. . . Passive alignment techniques not provided for in B81C 2203/054 - B81C 2203/055	
2203/058	. . Aligning components using methods not provided for in B81C 2203/051 - B81C 2203/052	
2203/07	. Integrating an electronic processing unit with a micromechanical structure	
2203/0707	. . Monolithic integration, i.e. the electronic processing unit is formed on or in the same substrate as the micromechanical structure	
2203/0714	. . . Forming the micromechanical structure with a CMOS process	
2203/0721	. . . Forming the micromechanical structure with a low-temperature process (B81C 2203/0735 takes precedence)	
2203/0728	. . . Pre-CMOS, i.e. forming the micromechanical structure before the CMOS circuit	
2203/0735	. . . Post-CMOS, i.e. forming the micromechanical structure after the CMOS circuit	
2203/0742	. . . Interleave, i.e. simultaneously forming the micromechanical structure and the CMOS circuit	
2203/075	. . . the electronic processing unit being integrated into an element of the micromechanical structure	
2203/0757	. . . Topology for facilitating the monolithic integration	
2203/0764 Forming the micromechanical structure in a groove	
2203/0771 Stacking the electronic processing unit and the micromechanical structure	
2203/0778 Topology for facilitating the monolithic integration not provided for in B81C 2203/0764 - B81C 2203/0771	
2203/0785	. . Transfer and join technology, i.e. forming the electronic processing unit and the micromechanical structure on separate substrates and joining the substrates	
2203/0792	. . . Forming interconnections between the electronic processing unit and the micromechanical structure	
2900/00	Apparatus specially adapted for the manufacture or treatment of microstructural devices or systems	
2900/02	. Microextrusion heads	